

ISC Silicon NPN Power Transistor

2SD2524

DESCRIPTION

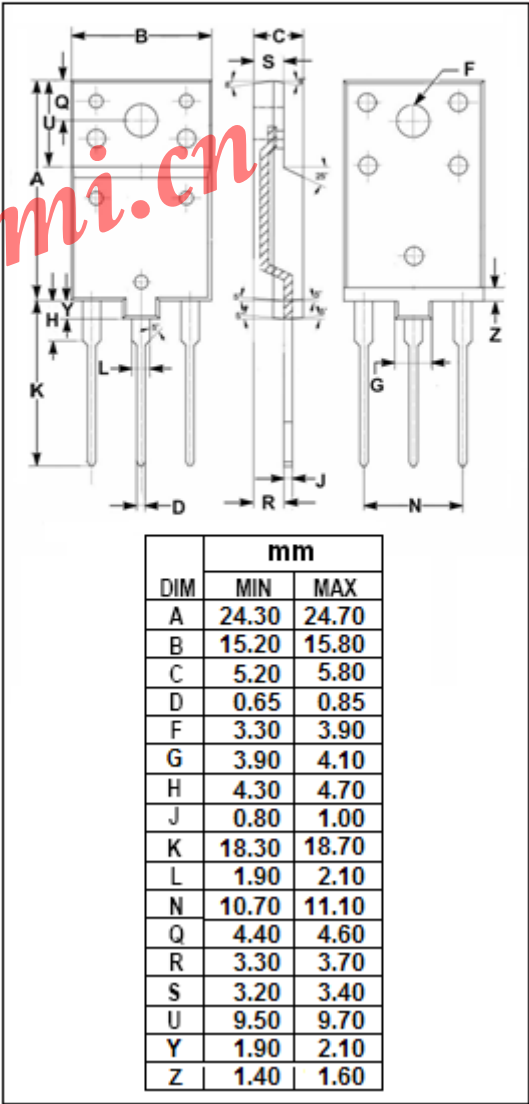
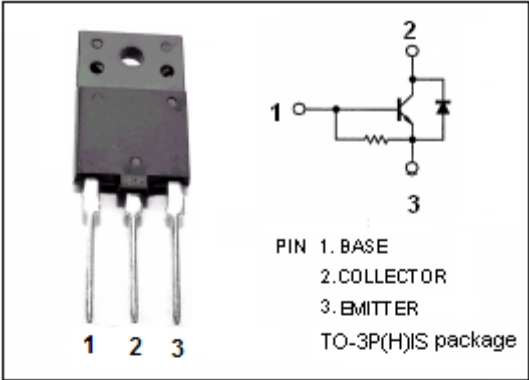
- High Breakdown Voltage-
: $V_{CBO}=1700V$ (Min)
- High Switching Speed
- Low Saturation Voltage
- Built-in Damper Diode

APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1700	V
V_{CES}	Collector-Emitter Voltage	1700	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	8	A
I_{CM}	Collector Current-Peak	20	A
I_{BM}	Base Current-Peak	5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	100	W
	Collector Power Dissipation @ $T_a=25^{\circ}C$	3	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



ISC Silicon NPN Power Transistor**2SD2524****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 500\text{mA}$; $I_C = 0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 6\text{A}$; $I_B = 2\text{A}$			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 6\text{A}$; $I_B = 2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 1000\text{V}$; $I_E = 0$			50	μA
		$V_{CB} = 1700\text{V}$; $I_E = 0$			1.0	mA
h_{FE}	DC Current Gain	$I_C = 6\text{A}$; $V_{CE} = 5\text{V}$	4		10	
V_{ECF}	C-E Diode Forward Voltage	$I_F = 8\text{A}$			2.0	V
f_T	Current-Gain—Bandwidth Product	$I_C = 0.1\text{A}$; $V_{CE} = 10\text{V}$		3		MHz

Resistive Load

t_s	Storage Time	$I_C = 6\text{A}$, $I_{B(end)} = 2\text{A}$, $L_{leak} = 5\text{ }\mu\text{H}$			12	μs
t_f	Fall Time				0.8	μs